10/593556 IAP9/Rec'd PCT/PTO 20 SEP 2006

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Michitaka OHTAKI

Application Number: Not yet assigned

(§371 of international application No. PCT/JP2005/005088)

Filed: September 20, 2006

For: POROUS THERMOELECTRIC MATERIAL AND PROCESS FOR

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PRODUCING THE SAME

Attorney Docket Number:

062925

Customer Number:

38834

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450 September 20, 2006

Sir:

In compliance with 37 C.F.R. §1.56, Applicants direct the attention of the Patent and Trademark Office to the documents listed on the attached PTO/SB/08. A copy of each non- U.S. document is enclosed herewith as well as an International Search Report mailed June 28, 2005.

If there are any fees due in connection with the filing of this paper, please charge Deposit Account No. 50-2866.

Respectfully submitted,

WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP

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Enclosure: PTO/SB/08, Documents (22) & Int'l Search Report

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known					
Application Number	Not yet assigned				
Confirmation Number					
Filing Date	September 20, 2006				
First Named Inventor	Michitaka OHTAKI				
Art Unit					
Examiner Name					
Attorney Docket Number	062925				

U.S. PATENT	DOCUMENTS

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of

Examiner Cite	Cita	Document Number		Publication Date		
Examiner Initials*	No.1	Number	Kind Code ² (if known)	MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	
	1	US 6,670,539	B2	12/30/2003	Delphi Technologies, Inc.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date	Name of Patentee or	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation
	2	JP	7-231121	Α	8/29/1995	Tokyo Tekko Co., Ltd.	Abstract; Cited in ISR
	3	JP	11-298052	Α	10/29/1999	Toshiba Corp	Abstract; Cited in ISR
	4	JP	11-317548	A	11/16/1999	Agency of Ind Science & Technol	Abstract; Cited in ISR
	5	JP	4-199859	A	7/21/1992	Matsushita Electric Industrial Co., Ltd.	Abstract; Cited in ISR Corresponds to #1
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	7	JP	2-69367	A	3/8/1990	Showa Denko KK	Abstract; Cited in ISR
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)					Confirmation Number			
					Filing Date	Septembe	r 20, 2006	
					First Named Inventor	Michitaka OHTAKI		
					Art Unit			
					Examiner Name			
	Sheet	2	of	2	Attorney Docket Number	062925		
Examiner	Cite	Include name of the auth	or (in CA	PITAL LETTERS), title o	f the article (when appropriate), title of age(s), volume-issue number(s), publishe	the item (book, er, city, and/or	Translation ⁶	
Initials*	No.1							
OHTAKI M. et al., "Thermoelectric properties of Al-doped ZnO sintered with nanosized void forming agents", Proc. 22 nd Int. Conf. Thermoelectrics, IEEE, Piscataway, pp. 171-174 (2003)								
International Search Report mailed June 28, 2005 of International Application PCT/JP2005/005088								
	1	PC1/3P2003/003088						

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.